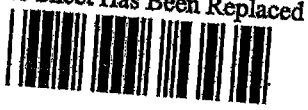
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ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device and a method of manufacturing the same. The surface of a substrate of an active region surrounded by an element isolation trench is horizontally flat in the center portion of the active region but falls toward the side wall of the element isolation trench in the shoulder portion of the active region. This inclined surface contains two inclined surfaces having different inclination angles. The first inclined surface near the center portion of the active region is relatively steep and the second inclined surface near the side wall of the element isolation trench is gentler than the first inclined surface. The surface of the substrate in the shoulder portion of the active region is wholly rounded and has no angular portion.